

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Bruno GHYSELEN et al.

Confirmation No.

Application No.:

Group Art Unit:

Filing Date:

Examiner:

For: FORMING STRUCTURES THAT INCLUDE A
RELAXED OR PSEUDO-RELAXED LAYER ON A
SUBSTRATE

Atty. Docket No.: 4717-10000

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to applicants' duty of disclosure under 37 C.F.R. 1.56, enclosed are copies of ten (10) references for the Examiner's review and consideration. These references were cited in the specification of the application and in preliminary search report and a copy is enclosed.

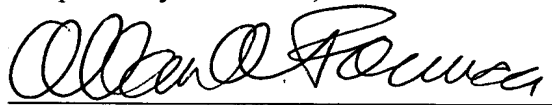
These references are listed on the enclosed Form PTO-1449. It is respectfully requested that these references be made of record in this application by the Examiner's completion and return of the PTO Form 1449.

No fee or certification is believed to be due for this submission since the references are being submitted concurrent with the filing of this application. Should any fees be required, however, please charge such fees to **Winston & Strawn** Deposit Account No. 50-1814.

Date: _____

2/20/04

Respectfully submitted,



Allan A. Fanucci (Reg. No. 30,256)

WINSTON & STRAWN LLP
CUSTOMER NO. 28765
(212) 294-3311

Enclosures

LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>				ATTY. DOCKET NO.:		APPLICATION NO.:	
				4717-10000			
				APPLICANT:			
				Bruno GHYSELEN et al.			
				FILING DATE:		GROUP:	
				February 20, 2004			
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	5,882,987	3/1999	Sirikrishnan	438	458	
	AB	2002/0072130 A1	6/2002	Cheng et al.	438	10	
	AC	2002/0168864 A1	11/2002	Cheng et al.	438	725	
	AD	2002/0146892 A1	10/2002	Notsu et al.	438	455	
	AE	2003/0013305 A1	1/2003	Sugii et al.	438	689	
	AF						
	AG						
	AI						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES NO
	AJ	EP 1 248 294 A2	10/2002	Europe			X
	AK	WO 99/53539	10/1999	PCT			X
	AL	WO/0243153A1 (w/English Abstract)	5/2002	PCT			X
	AM						X
	AN						X
	AO						
OTHER REFERENCES <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
	AP	T. Tezuka et al., XP001109835, High-Performance Strained Si-on-Insulator MOSFETs by Novel Fabrication Processes Utilizing Ge-Condensation Technique , Symposium On VLSI Tech., Digest of Technical Papers. Honolulu, NY:IEEE US, pp. 96-97 (2002)					
	AQ	S. Mantl et al., "Strain relaxation of epitaxial SGe layers on Si(100) improved by hydrogen implantation" Nuclear Instruments and Methods in Physics Research , Vol. 147, No. 1-4, pp. 29-34 (1999)					
EXAMINER				DATE CONSIDERED			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609 ; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							